



2N60-C

Power MOSFET

2A, 600V N-CHANNEL POWER MOSFET

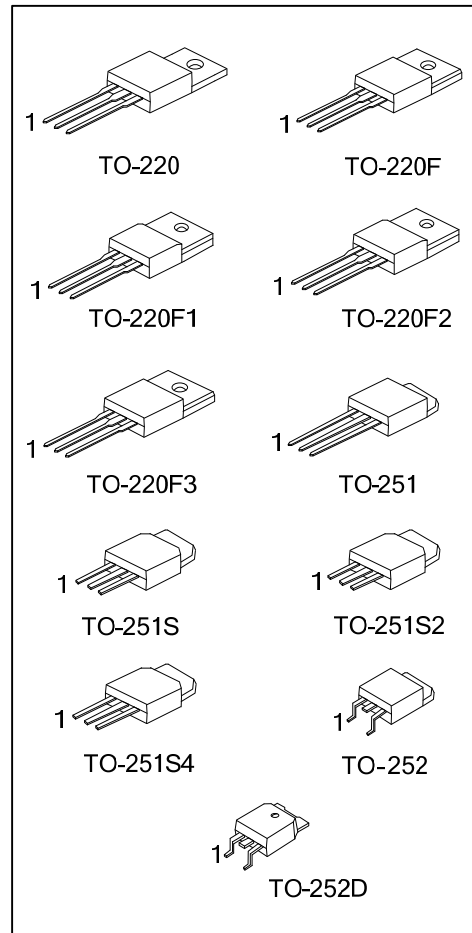
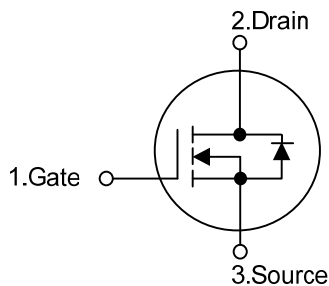
DESCRIPTION

The UTC **2N60-C** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 4.6 \Omega @ V_{GS} = 10V, I_D = 1A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



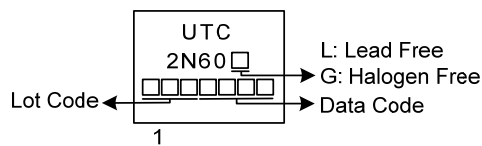
ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|----------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 2N60L-TA3-T | 2N60G-TA3-T | TO-220 | G | D | S | Tube |
| 2N60L-TF3-T | 2N60G-TF3-T | TO-220F | G | D | S | Tube |
| 2N60L-TF1-T | 2N60G-TF1-T | TO-220F1 | G | D | S | Tube |
| 2N60L-TF2-T | 2N60G-TF2-T | TO-220F2 | G | D | S | Tube |
| 2N60L-TF3T-T | 2N60G-TF3T-T | TO-220F3 | G | D | S | Tube |
| 2N60L-TM3-T | 2N60G-TM3-T | TO-251 | G | D | S | Tube |
| 2N60L-TMS-T | 2N60G-TMS-T | TO-251S | G | D | S | Tube |
| 2N60L-TMS2-T | 2N60G-TMS2-T | TO-251S2 | G | D | S | Tube |
| 2N60L-TMS4-T | 2N60G-TMS4-T | TO-251S4 | G | D | S | Tube |
| 2N60L-TN3-R | 2N60G-TN3-R | TO-252 | G | D | S | Tape Reel |
| 2N60L-TND-R | 2N60G-TND-R | TO-252D | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|---|---|
| <p>2N60L-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p> | <p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F3, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4, TN3: TO-252, TND: TO-252D</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p> |
|---|---|

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|---|-----------|------------|------------------|
| Drain-Source Voltage | | V_{DSS} | 600 | V |
| Gate-Source Voltage | | V_{GSS} | ± 30 | V |
| Avalanche Current (Note 2) | | I_{AR} | 2.0 | A |
| Drain Current | Continuous | I_D | 2.0 | A |
| | Pulsed (Note 2) | I_{DM} | 8.0 | A |
| Avalanche Energy | Single Pulsed (Note 3) | E_{AS} | 140 | mJ |
| | Repetitive (Note 2) | E_{AR} | 4.5 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 3.7 | V/ns |
| Power Dissipation | TO-220 | P_D | 54 | W |
| | TO-220F/TO-220F1 | | 23 | |
| | TO-220F3 | | | |
| | TO-220F2 | | 24 | |
| | TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D | | 44 | |
| Junction Temperature | | T_J | +150 | $^\circ\text{C}$ |
| Operating Temperature | | T_{OPR} | -55 ~ +150 | $^\circ\text{C}$ |
| Storage Temperature | | T_{STG} | -55 ~ +150 | $^\circ\text{C}$ |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L=70\text{mH}$, $I_{AS}=2.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 2\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---------------------|---|---------------|---------|---------------------------|
| Junction to Ambient | TO-220F/TO-220F1/ TO-220F2/TO-220F3 | θ_{JA} | 62.5 | $^\circ\text{C}/\text{W}$ |
| | TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D | | 100 | |
| Junction to Case | TO-220F/TO-220F1 TO-220F3 | θ_{JC} | 5.5 | $^\circ\text{C}/\text{W}$ |
| | TO-220F2 | | 5.43 | |
| | TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D | | 2.87 | |
| | | | | |

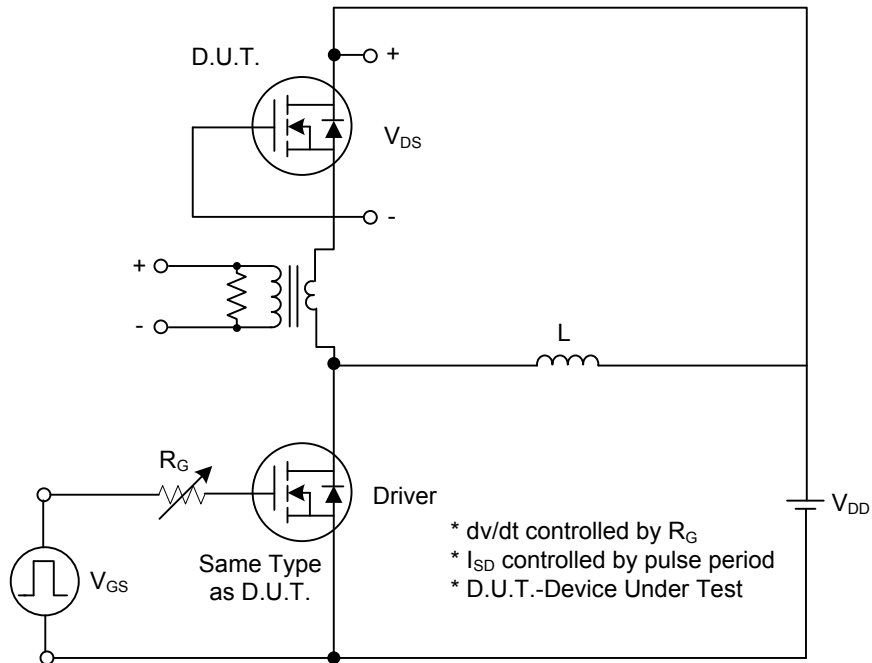
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|------------------------------|---|-----|-----|------|--------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 600 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS} = 600V, V_{GS} = 0V$ | | | 10 | μA |
| | | $V_{DS} = 480V, T_C = 125^\circ C$ | | | 100 | μA |
| Gate-Source Leakage Current | Forward | I_{GSS} | | | 100 | nA |
| | Reverse | | | | | |
| | | $V_{GS} = -30V, V_{DS} = 0V$ | | | -100 | nA |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_J$ | $I_D=250\mu A$, Referenced to $25^\circ C$ | | 0.4 | | $V/^\circ C$ |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS} = 10V, I_D = 1A$ | | | 4.6 | Ω |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{ISS} | $V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$ | | 300 | 350 | pF |
| Output Capacitance | C_{OSS} | | | 45 | 50 | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | 10 | 13 | pF |
| SWITCHING CHARACTERISTICS | | | | | | |
| Total Gate Charge | Q_G | $V_{DS}=50V, V_{GS}=10V, I_D=1.3A$ $I_G = 100\mu A$ (Note 1, 2) | | 35 | | nC |
| Gate-Source Charge | Q_{GS} | | | 3.5 | | nC |
| Gate-Drain Charge | Q_{GD} | | | 2.5 | | nC |
| Turn-On Delay Time | $t_{D(ON)}$ | $V_{DD} = 30V, I_D = 0.5A, R_G = 25\Omega,$ $V_{GS} = 10V$ (Note 1, 2) | | 30 | | ns |
| Turn-On Rise Time | t_R | | | 25 | | ns |
| Turn-Off Delay Time | $t_{D(OFF)}$ | | | 90 | | ns |
| Turn-Off Fall Time | t_F | | | 25 | | ns |
| DRAIN-SOURCE DIODE CHARACTERISTICS | | | | | | |
| Drain-Source Diode Forward Voltage | V_{SD} | $V_{GS} = 0V, I_{SD} = 2.0A$ | | | 1.4 | V |
| Continuous Drain-Source Current | I_{SD} | | | | 2.0 | A |
| Pulsed Drain-Source Current | I_{SM} | | | | 8.0 | A |
| Reverse Recovery Time | t_{rr} | $V_{GS} = 0V, I_{SD} = 2A,$ $di/dt = 100 A/\mu s$ (Note 1) | | 275 | | ns |
| Reverse Recovery Charge | Q_{RR} | | | 1.1 | | μC |

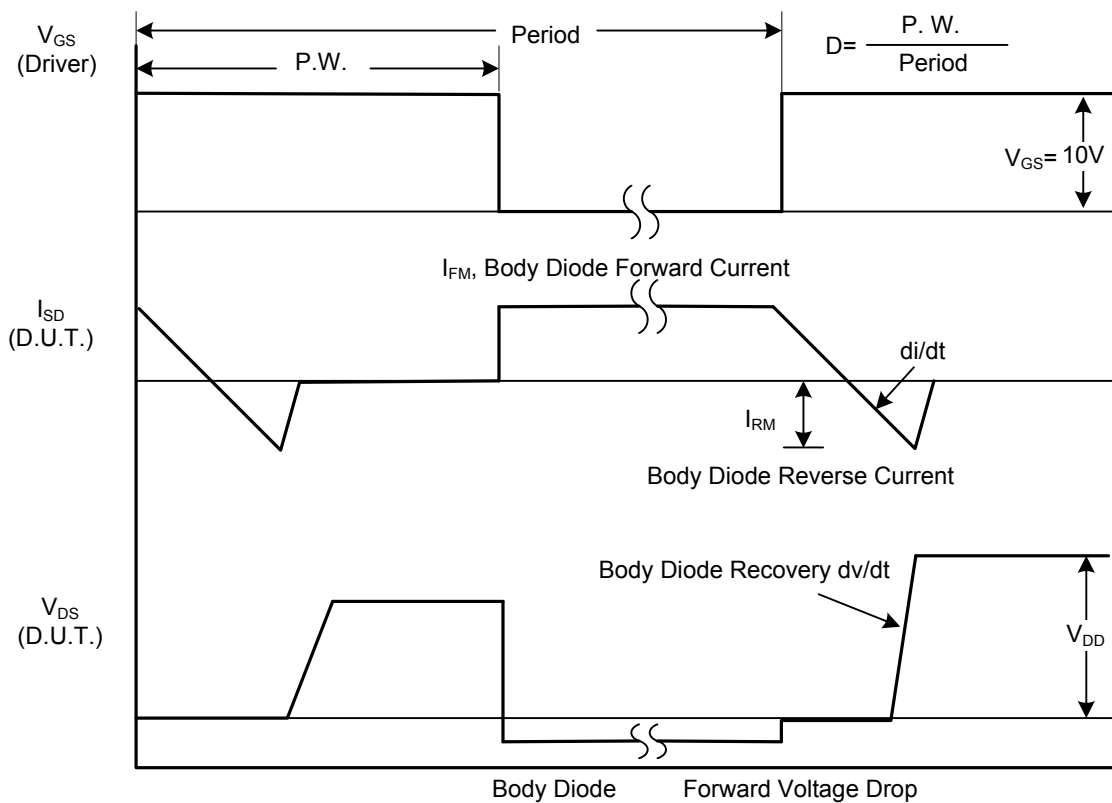
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

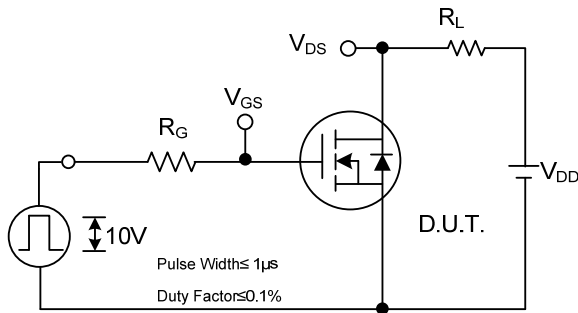


Peak Diode Recovery dv/dt Test Circuit

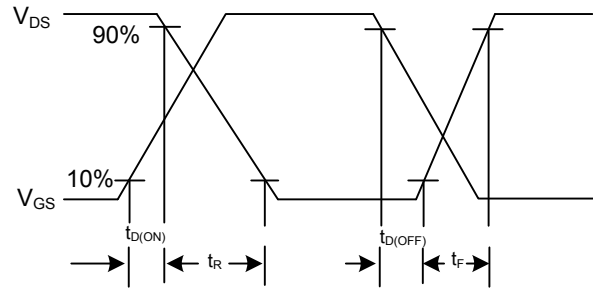


Peak Diode Recovery dv/dt Waveforms

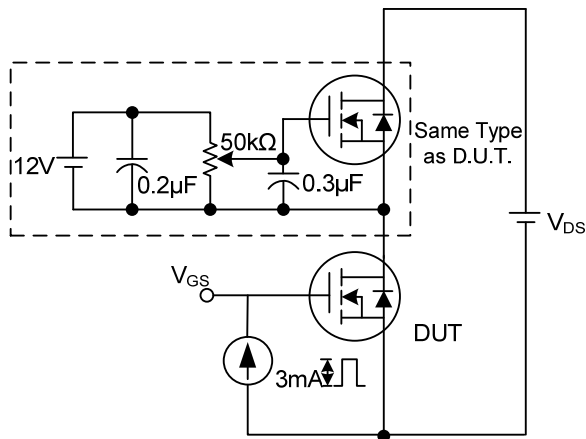
TEST CIRCUITS AND WAVEFORMS (Cont.)



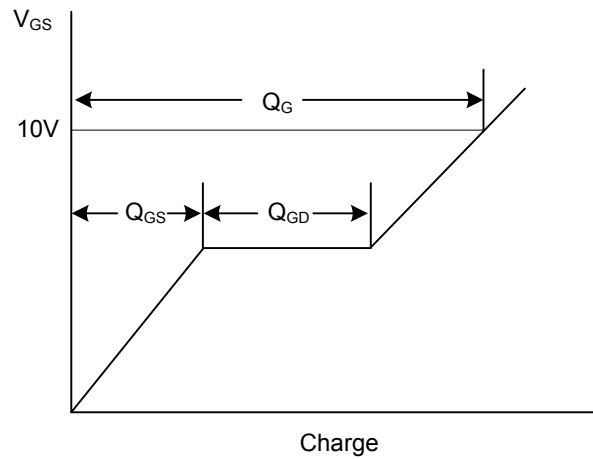
Switching Test Circuit



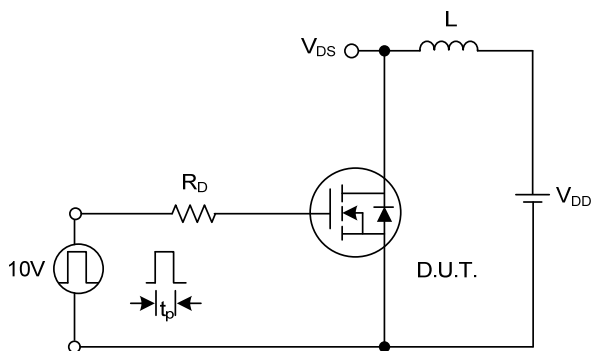
Switching Waveforms



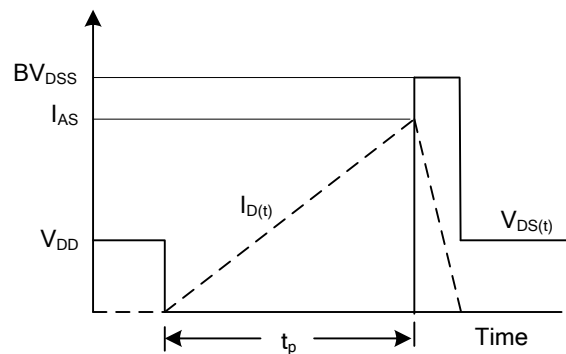
Gate Charge Test Circuit



Gate Charge Waveform

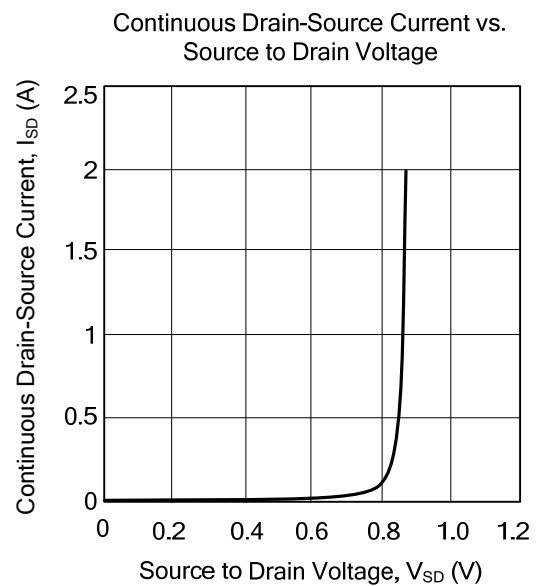
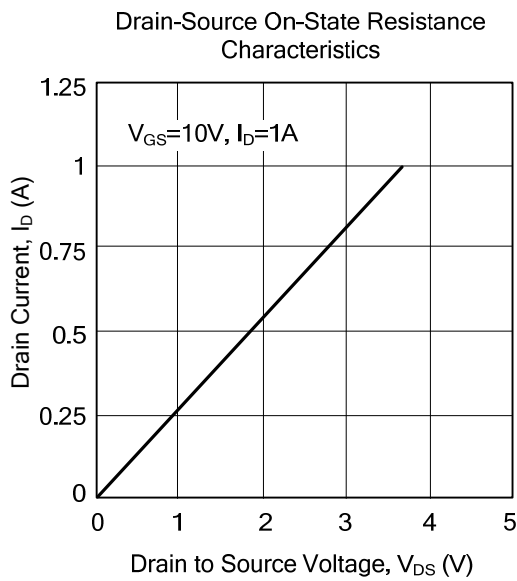
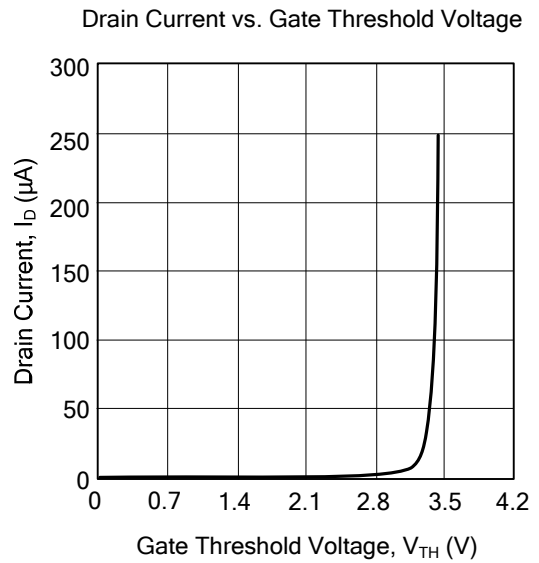
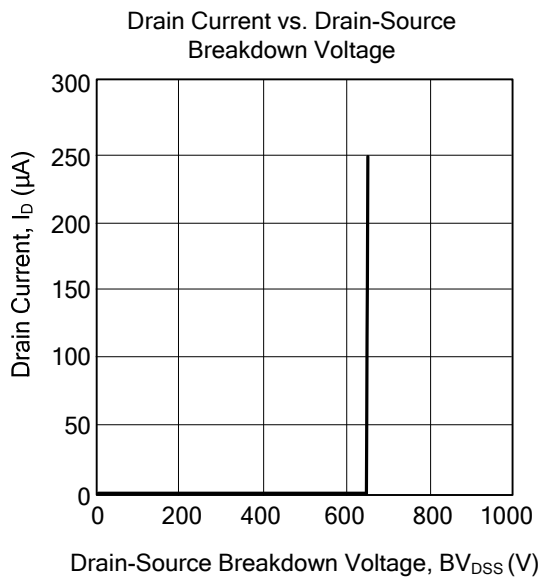


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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